

TO-92 Plastic-Encapsulate Transistors

KSA643 TRANSISTOR (PNP)

FEATURE

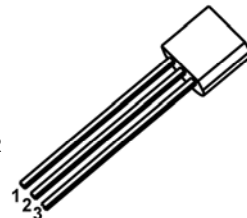
- Collector dissipation
- Complement to KSD261

MAXIMUM RATINGS (T_a=25°C unless otherwise noted)

Symbol	Parameter	Value	Unit
V _{CB0}	Collector-Base Voltage	-40	V
V _{CEO}	Collector-Emitter Voltage	-20	V
V _{EBO}	Emitter-Base Voltage	-5	V
I _C	Collector Current -Continuous	-500	mA
P _C	Collector Power Dissipation	500	mW
T _J	Junction Temperature	150	°C
T _{stg}	Storage Temperature	-55-150	°C

TO-92

1. EMITTER
2. BASE
3. COLLECTOR



ELECTRICAL CHARACTERISTICS (T_a=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	V _{(BR)CBO}	I _C = -100μA, I _E =0	-40			V
Collector-emitter breakdown voltage	V _{(BR)CEO}	I _C = -10mA, I _B =0	-20			V
Emitter-base breakdown voltage	V _{(BR)EBO}	I _E = -10μA, I _C =0	-5			V
Collector cut-off current	I _{CBO}	V _{CB} = -25 V, I _E =0			-0.2	μA
Emitter cut-off current	I _{EBO}	V _{EB} = -3 V, I _C =0			-0.2	μA
DC current gain	h _{FE} *	V _{CE} = -1 V, I _C = -100mA	40		400	
Collector-emitter saturation voltage	V _{CE(sat)} *	I _C = -500mA, I _B = -50mA			-0.4	V
Base-emitter saturation voltage	V _{BE(sat)} *	I _C = -500mA, I _B = -50mA			-1.3	V

* PULSE TEST

CLASSIFICATION OF h_{FE}

Rank	R	O	Y	G
Range	40-80	70-140	120-240	200-400